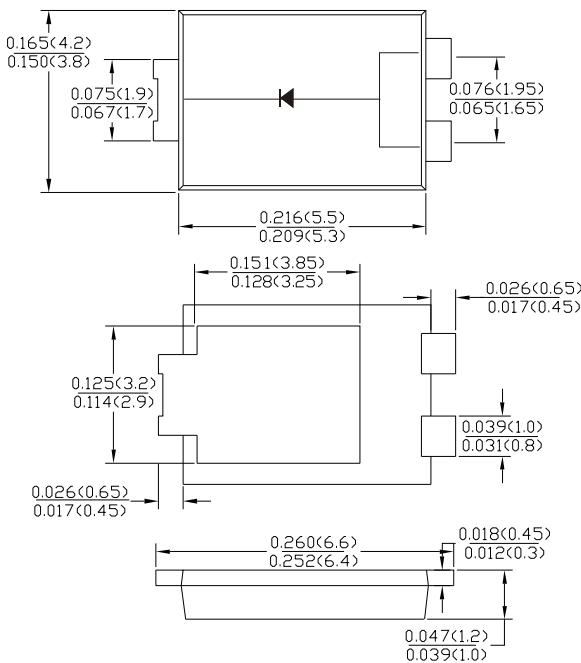


Features

- Schottky Barrier Chip
- High Thermal Reliability
- Patented Super Barrier Rectifier Technology
- High Forward Surge Capability
- Ultra Low Power Loss, High Efficiency
- Excellent High Temperature Stability
- Plastic material-UL flammability 94V-0

TO-277B

dimensions in inches and (millimeters)

Maximum Ratings and Electrical Characteristics @ $T_A = 25^\circ C$ unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Parameter	Symbol	SB1045L	SB1050L	SB1060L	SB1080L	SB10100L	Unit
Peak Repetitive Reverse Voltage	V_{RRM}						
Working Peak Reverse Voltage	V_{RWM}	45	50	60	80	100	V
DC blocking voltage	V_{DC}						
RMS Rectified Voltage	$V_{R(RMS)}$	32	35	42	56	70	V
Average Rectified Output Current (Note1)	IF(AV)			10			A
Non-Repetitive Peak Forward Surge8.3ms							
Single Half Sine-Wave Superimposed on rated load(JEDEC Method) (Note2)	I_{FSM}			150			A
I^2t Rating for Fusing ($t < 8.3\text{ms}$)	I^2t			93.375			A^2s
Forward Voltage Drop $T_A = 25^\circ C$ @IF=10A	V_{FM}		0.50	0.55	0.75		V
Peak Reverse Current $T_A = 25^\circ C$ At Rated DC Blocking Voltage $T_A = 100^\circ C$	I_R		0.3	15			mA
Typical Thermal Resistance Junction to Ambient	$R_{\theta JA}$		80				$^\circ\text{C/W}$
	$R_{\theta JL}$		10				
Operating junction temperature range	T_J		-55 to +150				$^\circ\text{C}$
storage temperature range	T_{STG}		-55 to +150				$^\circ\text{C}$

Note:1.Valid Provided that are kept at ambient temperature at a distance of 9.5mm from the case.

2.Fr-4pcb.2oz.Copper,minimum recommend pad layout .18.8mm×14.4.Anode pad dimensions 5.6mm×14.4mm.

Fig.1 - Forward Current Derating Curve

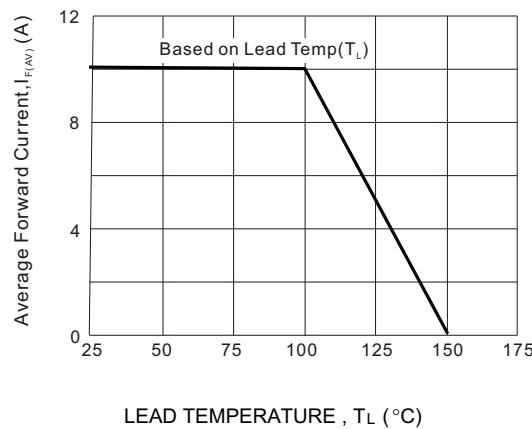


Fig2 : Instantaneous Forward Voltage

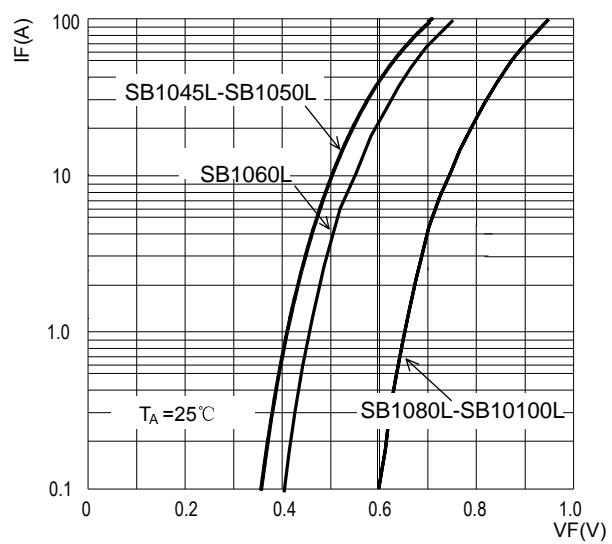


Fig3: Surge Forward Current Capability

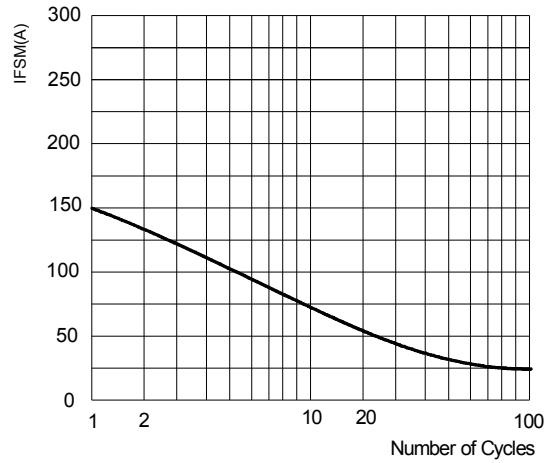


Fig4: Typical Reverse Characteristics

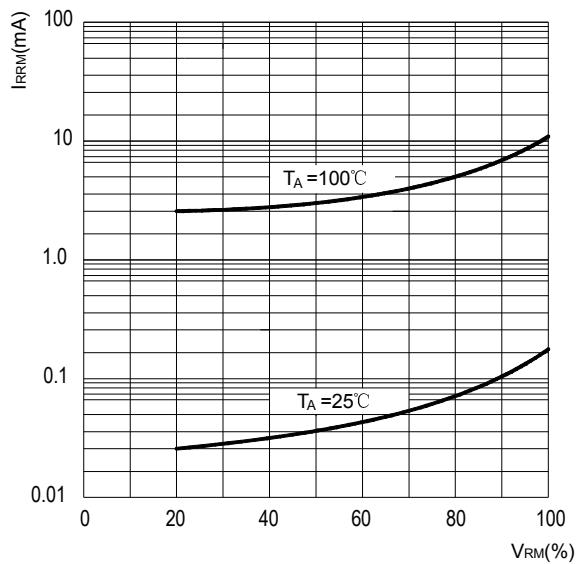


FIG.5 MOUNTING PAD LAYOUT

